

PDNM6T20V6

N-Channel MOSFET

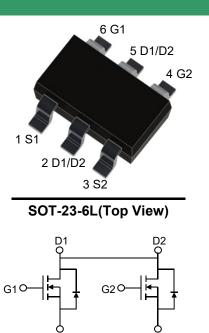
Feature

- Surface Mount Package
- Lead free product is acquired
- High Power and current handing capability

| MOSFET Product Summary | | | | |
|------------------------|----------------------------|--------------------|--|--|
| V _{DS} (V) | R _{DS(on)} (mΩ) | I _D (A) | | |
| 19.5 | 18@ V _{GS} = 4.5V | 6.0 | | |

Applications

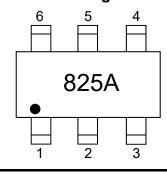
- Battery Protection
- Battery Powered Systems
- > Power Management in Notebook Computer



Circuit Diagram

S2

S1



Marking (Top View)

Mechanical Data

- Case: SOT23-6L
- Case Material: "Green" Molding Compound.
 UL-Flammability Classification Rating 94V-0.
- > Weight: 0.15 grams (approximate) .

Absolute maximum rating@25°C

| Rating | Symbol | Value | Units |
|--|----------------------------------|----------|-------|
| Drain-Source Voltage | V _{DS} | 19.5 | V |
| Gate-Source Voltage | V _{GS} | ±12 | V |
| Drain Current-Continuous ¹⁾ | I _D | 6.0 | A |
| Pulsed Drain Current ²⁾ | I _{DM} | 20 | A |
| Total Power Dissipation ³⁾ | P _D | 1.9 | w |
| Thermal Resistance Junction-to-Ambient ³⁾ | R _{eja} | 65 | °C/W |
| Junction and Storage Temperature Range | T _{J,} T _{STG} | -55~+150 | °C |

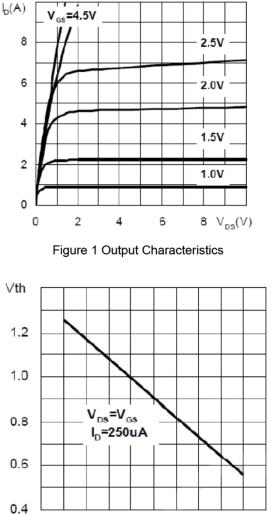
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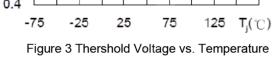
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Units |
|---|---------------------|--|----------|------|------|-------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_{D} = 250 \mu A$ | 19.5 | 21 | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 19V, V_{GS} = 0V$ | - | - | 1.0 | μA |
| Gate-Body Leakage Current | I _{GSS} | V_{GS} = ±12V, V_{DS} = 0V | - | - | ±100 | nA |
| On Characteristics ⁴⁾ | | | | • | - | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 0.5 | 0.7 | 1.2 | V |
| | 5 | V _{GS} = 4.5V,I _D = 6.0A | - | 18 | 23 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} = 2.5V,I _D = 2.0A | - | 22 | 30 | |
| Diode Forward Voltage | V _{SD} | V _{GS} = 0V,I _S = 1A | - | 0.8 | 1.3 | V |
| Dynamic Characteristics ⁵⁾ | | | | | · | |
| Input Capacitance | C _{lss} | V _{DS} = 10V,V _{GS} = 0V, f = 1.0MHz | - | 370 | - | pF |
| Output Capacitance | C _{oss} | | - | 89 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 10 | - | |
| Switching Characteristics ⁵⁾ | | | <u>.</u> | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 200 | - | |
| Turn-on Rise Time | t _r | $V_{DS} = 10V, V_{GS} = 4.5V,$ $R_{G} = 10\Omega, I_{D} = 3A$ | - | 236 | - | |
| Turn-Off Delay Time | t _{d(off)} | | - | 36 | - | ns . |
| Turn-Off Fall Time | t _f | | - | 165 | - | |
| Total Gate Charge | Q _g | | - | 7.5 | - | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 16V, V_{GS} = 4.5V,$ $I_{D} = 6A$ | - | 3.0 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 1.5 | - | 1 |

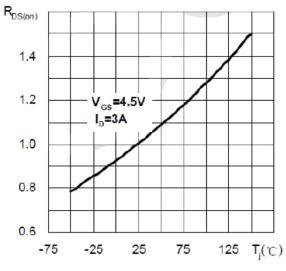
Notes:

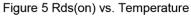
Notes:
 Pulse width limited by maximum junction temperature.
 Pulse test : Pulse width ≤ 100µs, duty cycle ≤ 2%.
 Device mounted on 1 inch FR4 PCB with 2oz.Copper.
 Measured under pulsed conditions. Pulse width ≤ 300µs, duty cycle ≤ 2%.
 Guaranteed by design, not subject to production.

Typical Characteristics (N-Channel)











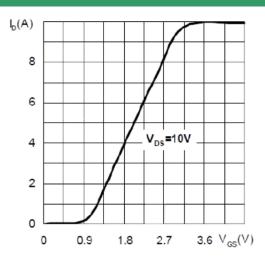


Figure 2 Transfer Characteristics

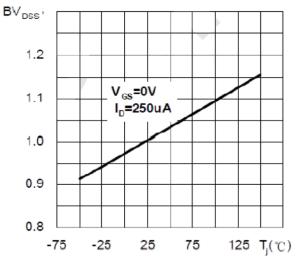


Figure 4 BVDSS vs. Temperature

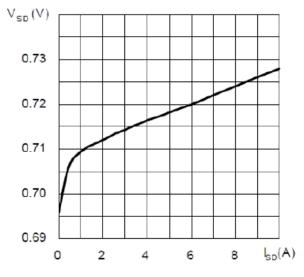


Figure 6 Source to Drain vs. Temperature

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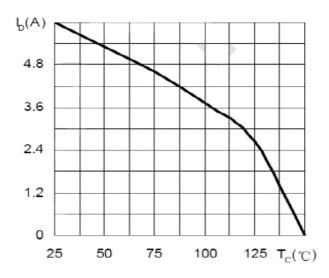


Figure 7 Maximum Drain Current vs. Case Temperature

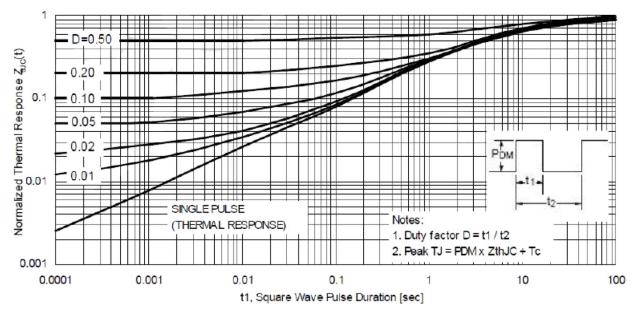
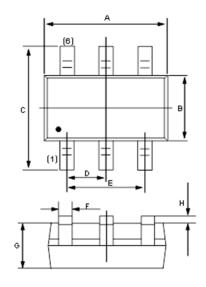
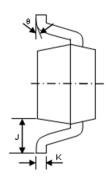


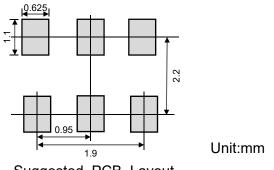
Figure 8 Maximum Transient Thermal Impedence

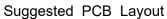
Product dimension (SOT-23-6L)





| Dim | Millimeters | | Inches | |
|-----|-------------|------------|------------|-------|
| | Min | Мах | Min | Мах |
| А | 2.85 | 3.15 | 0.112 | 0.124 |
| В | 1.55 | 1.75 | 0.061 | 0.069 |
| С | 2.60 | 3.00 | 0.102 | 0.118 |
| D | 0.85 | 1.05 | 0.033 | 0.041 |
| E | 1.70 | 2.10 | 0.067 | 0.083 |
| F | 0.39 | 0.49 | 0.015 | 0.019 |
| G | 0.90 | 1.30 | 0.035 | 0.051 |
| Н | 0.00 | 0.15 | 0.000 | 0.006 |
| J | 0.59 Ref. | | 0.023 Ref. | |
| К | 0.12 | 0.19 | 0.005 | 0.007 |
| θ | 0 ° | 8 ° | 0 ° | 8° |





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